

**AMENDMENTS TO THE ABSTRACT**

Please replace the abstract with the following amended abstract:

Disclosed is a method of manufacturing a semiconductor device. A floating gate is formed and a nitridation process is then implemented. With the disclosed process, ~~it~~ it is thus possible to improve the roughness of the top surface of the floating gate electrode. Furthermore, a nitridation process and a dielectric film formation process are implemented in-situ. ~~It is possible to simplify~~ which simplifies the manufacturing process.